



SD1019-02

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SD1019-02** is Designed for
VHF Communications up to 136 MHz

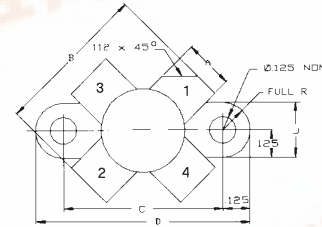
FEATURES:

- **P_G** = 4.5 dB Minimum at 150 MHz
- **Omnigold™** Metallization System

MAXIMUM RATINGS

I_C	9.0 A
V_{CB}	65 V
V_{CE}	35 V
P_{DISS}	117 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	1.7°C/W

PACKAGE STYLE .380 4 LEAD FLG



	MINIMUM Increase/yr	MAXIMUM Increase/yr
A	250/5.35	230/5.84
B	785/18.94	
C	778/18.29	738/16.54
D	970/24.64	560/12.89
E		309/6.78
F	604/13.10	886/20.16
G	895/21.16	1155/26.67
H	160/4.86	108/4.57
I		293/7.11
J	342/6.12	255/6.40

1 = COLLECTOR 3 & 4 = EMITTER 2 = BASE

CHARACTERISTICS $T_C = 25^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 20\text{ mA}$	65			V
BV_{CEO}	$I_C = 200\text{ mA}$	35			V
BV_{EBO}	$I_E = 10\text{ mA}$	4.0			V
I_{CBO}	$V_{CB} = 30\text{ V}$		1.5		mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 500\text{ mA}$	5.0			---
C_{OB}	$V_{CB} = 30\text{ V}$ $f = 1.0\text{ MHz}$			150	pF
P_{OUT} P_G	$V_{CC} = 13.5\text{ V}$ $P_{IN} = 10.6\text{ W}$ $f = 150\text{ MHz}$	30 4.5			W dB

